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NXP Semiconductors/Freescale Semiconductor, Inc. BYC8X-600P,127

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Datasheet of BYC8X-600P,127 - DIODE GEN PURP 600V 8A TO220F

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Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 75 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	8	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_h \le$ 75 °C; squarewave pulse	-	-	16	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	_	91	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	-	100	А
Static characte	eristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I _F = 8 A; T _j = 150 °C	-	1.4	-	V
		1		1		







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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic char	Dynamic characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	12	18	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	19	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYC8X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113		

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC8X-600P	BYC8X-600P

BYC8X-600P

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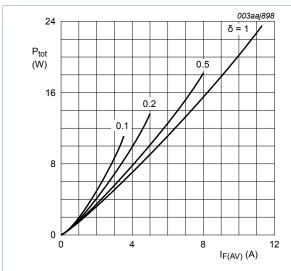
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Limiting values

Table 5. **Limiting values**

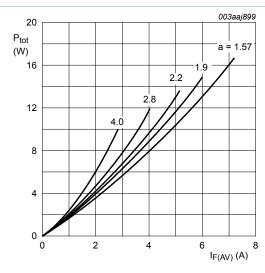
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 75 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 $\mu s;$ $T_h \leq$ 75 °C; squarewave pulse	-	16	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	91	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	100	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C



Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_O &= 1.581 \text{ V; } R_S = 0.043 \text{ } \Omega \end{split}$$



Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

 $V_O = 1.581 \text{ V}; R_S = 0.043 \Omega$

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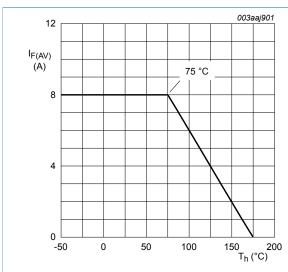


Fig. 3. Average forward current as a function of heatsink temperature; maximum values

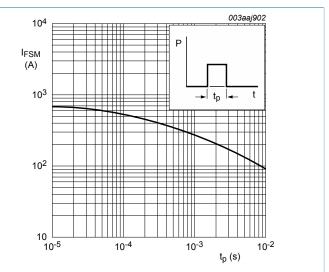


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance	without heatsink compound	-	-	7.2	K/W
	from junction to heatsink	with heatsink compound; Fig. 5	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	60	-	K/W

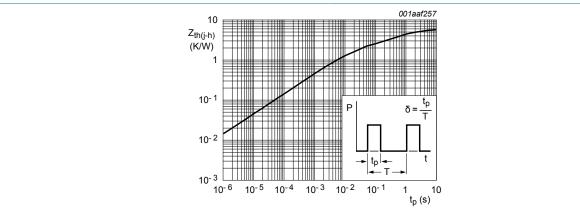


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse width

10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF



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11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I _F = 8 A; T _j = 150 °C	-	1.4	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	20	μΑ
		V _R = 600 V; T _j = 125 °C	-	-	200	μA
Dynamic c	haracteristics					
Q _r	recovered charge	I_F = 8 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; Fig. 7	-	17	-	nC
		I_F = 8 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 125 °C; Fig. 7	-	90	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	12	18	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	19	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	A
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	6	А



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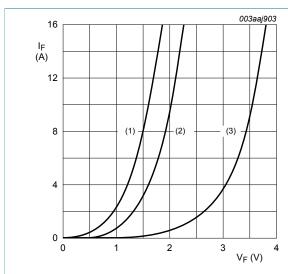


Fig. 6. Forward current as a function of forward voltage

(1) $T_j = 125$ °C; typical values;

(2) $T_i = 125$ °C; maximum values;

(3) $T_i = 25$ °C; maximum values;

 $V_O = 1.581 \text{ V}; R_S = 0.043 \Omega$

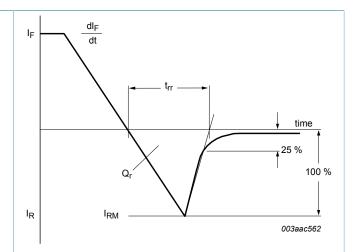


Fig. 7. Reverse recovery definitions; ramp recovery

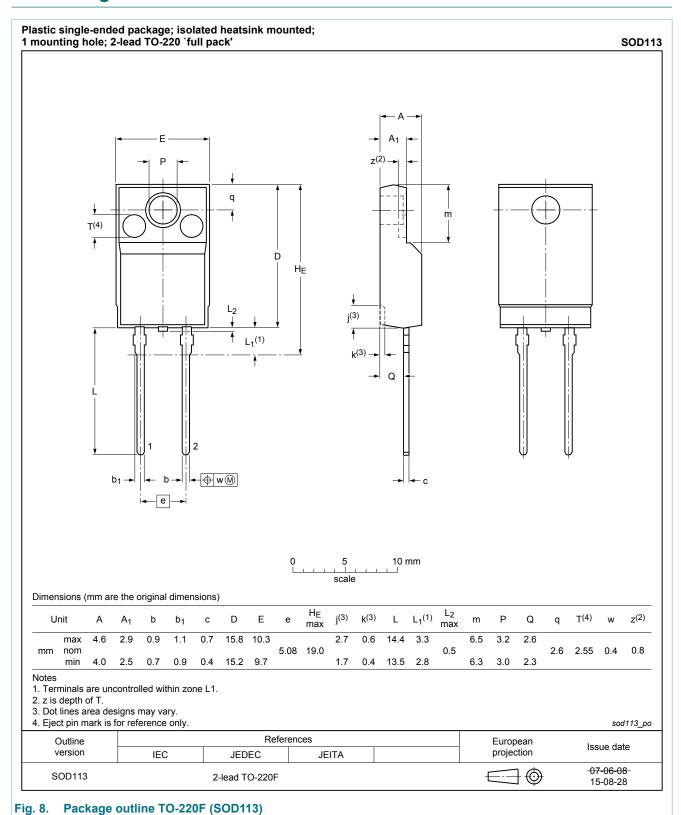


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12. Package outline



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13.1 Data sheet status

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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